

June 2009

CNY171M, CNY172M, CNY173M, CNY174M, CNY17F1M, CNY17F2M, CNY17F3M, CNY17F4M, MOC8106M, MOC8107M Phototransistor Optocouplers

Features

- UL recognized (File # E90700, Vol. 2)
- VDE recognized
 - Add option V (e.g., CNY17F2VM)
 - File #102497
- Current transfer ratio in select groups
- High BV_{CEO}: 70V minimum (CNY17XM, CNY17FXM, MOC810XM)
- Closely matched current transfer ratio (CTR) minimizes unit-to-unit variation.
- Very low coupled capacitance along with no chip to pin 6 base connection for minimum noise susceptability (CNY17FXM, MOC810XM)

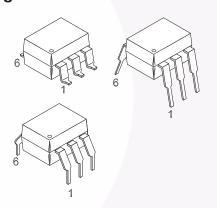
Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls

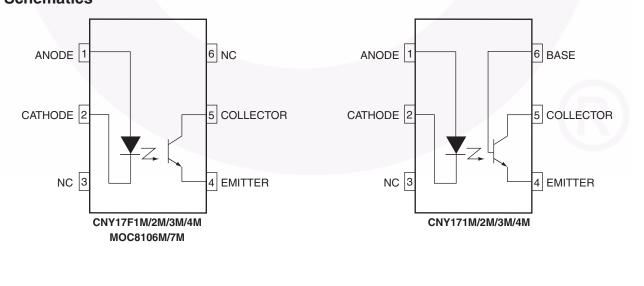
Description

The CNY17XM, CNY17FXM and MOC810XM devices consist of a Gallium Arsenide IRED coupled with an NPN phototransistor in a dual in-line package.

Package Outlines



Schematics



©2006 Fairchild Semiconductor Corporation CNY17XM, CNY17FXM, MOC810XM Rev. 1.0.9

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Value	Units
TOTAL DE	VICE		
T _{STG}	Storage Temperature	-40 to +150	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
T _{SOL}	Lead Solder Temperature	260 for 10 sec	°C
P _D	Total Device Power Dissipation @ 25°C (LED plus detector)	250	mW
	Derate Linearly From 25°C	2.94	mW/°C
EMITTER			
I _F	Continuous Forward Current	60	mA
V _R	Reverse Voltage	6	V
I _F (pk)	Forward Current – Peak (1µs pulse, 300pps)	1.5	Α
P _D	LED Power Dissipation 25°C Ambient	120	mW
	Derate Linearly From 25°C	1.41	mW/°C
DETECTO	₹		
I _C	Continuous Collector Current	50	mA
V _{CEO}	Collector-Emitter Voltage	70	V
V _{ECO}	Emitter Collector Voltage	7	V
P _D	Detector Power Dissipation @ 25°C	150	mW
	Derate Linearly from 25°C	1.76	mW/°C

Electrical Characteristics (T_A = 25°C Unless otherwise specified.)⁽¹⁾

Individual Component Characteristics

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units
EMITTER		1	1				
V _F	Input Forward Voltage	I _F = 60mA	CNY17XM, CNY17FXM	1.0	1.35	1.65	V
		I _F = 10mA	MOC810XM	1.0	1.15	1.50	
CJ	Capacitance	$V_F = 0 V, f = 1.0MHz$	All		18		pF
I _R	Reverse Leakage Current	V _R = 6V	All		0.001	10	μA
DETECTO	DR				•		
BV _{CEO}	Breakdown Voltage Collector to Emitter	I _C = 1.0mA, I _F = 0	All	70	100		V
BV _{CBO}	Collector to Base	$I_C = 10\mu A, I_F = 0$	CNY171M/2M/3M/4M	70	120		
BV _{ECO}	Emitter to Collector	$I_E = 100 \mu A, I_F = 0$	All	7	10		
I _{CEO}	Leakage Current Collector to Emitter	V _{CE} = 10 V, I _F = 0	All		1	50	nA
I _{CBO}	Collector to Base	V _{CB} = 10 V, I _F = 0	CNY171M/2M/3M/4M	\		20	nA
C _{CE}	Capacitance Collector to Emitter	V _{CE} = 0, f = 1MHz	All		8		pF
C _{CB}	Collector to Base	V _{CB} = 0, f = 1MHz	CNY171M/2M/3M/4M		20		pF
C _{EB}	Emitter to Base	V _{EB} = 0, f = 1MHz	CNY171M/2M/3M/4M		10		pF

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	f = 60 Hz, t = 1 sec., $I_{I-O} \le 2\mu A^{(4)}$	7500			Vac(pk)
R _{ISO}	Isolation Resistance	$V_{I-O} = 500 VDC^{(4)}$	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance	$V_{I-O} = \emptyset$, f = 1MHz ⁽⁴⁾		0.2		pF

Transfer Characteristics ($T_A = 25^{\circ}C$ Unless otherwise specified.)⁽³⁾

Symbol	DC Characteristics		Test Conditions	Min.	Тур.*	Max.	Units
COUPLE	D						
(CTR) ⁽²⁾	Output Collector	MOC8106M	I _F = 10mA, V _{CE} = 10V	50		150	%
	Current	MOC8107M		100		300	
		CNY17F1M	I _F = 10mA, V _{CE} = 5V	40		80	
		CNY17F2M		63		125	3)
		CNY17F3M		100		200	
		CNY17F4M		160		320	
		CNY171M		40		80	
		CNY172M		63		125	
		CNY173M		100		200	
		CNY174M		160		320	
V _{CE(sat)}	Collector-Emitter	CNY17XM/FXM	I _C = 2.5mA, I _F = 10mA			0.4	V
	Saturation Voltage	MOC8106M/7M	$I_C = 500\mu A, I_F = 5.0mA$				

^{*}All typicals at $T_A = 25$ °C

Electrical Characteristics (Continued) (T_A = 25°C Unless otherwise specified.)⁽¹⁾

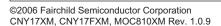
Transfer Characteristics (Continued)(3)

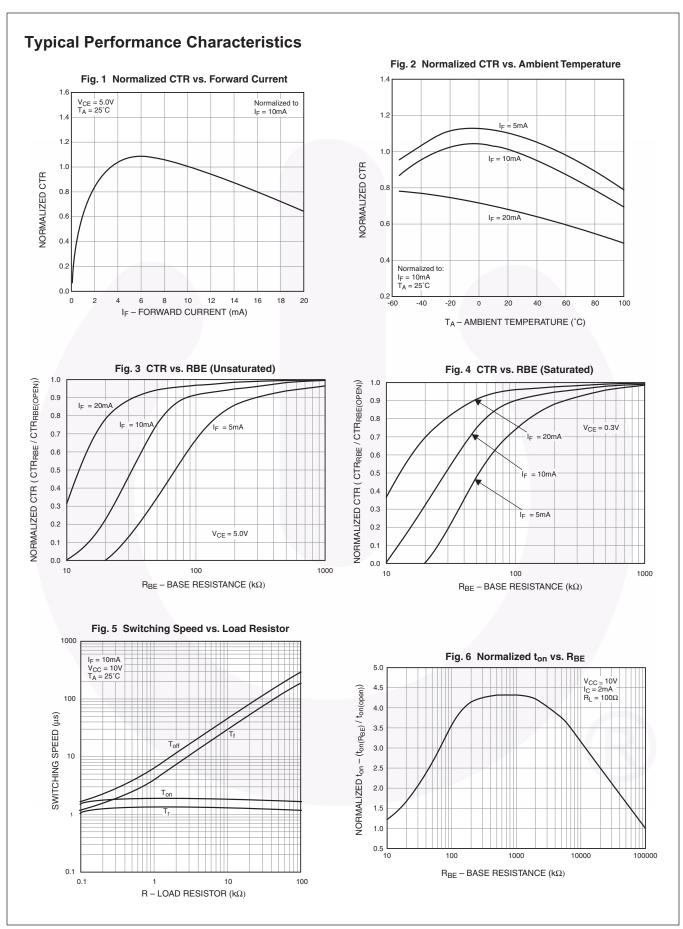
Symbol	AC Characteristics ⁽⁴⁾		Test Conditions	Min.	Тур.*	Max.	Units
NON-SAT	URATED SWITC	HING TIME					
t _{on}	Turn-On Time	All Devices	$I_C = 2.0$ mA, $V_{CC} = 10$ V, $R_L = 100\Omega$		2	10	μs
t _{off}	Turn-Off Time	All Devices	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$		3	10	μs
t _d	Delay Time	CNY17XM/XFM	$I_F = 10$ mA, $V_{CC} = 5$ V, $R_L = 75\Omega$			5.6	μs
t _r	Rise Time	All Devices	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$		1		μs
		CNY17XM/FXM	$I_F = 10 \text{mA}, V_{CC} = 5 \text{V}, R_L = 75 \Omega$			4.0	
t _s	Storage Time	CNY17XM/FXM	$I_F = 10 \text{mA}, V_{CC} = 5 \text{V}, R_L = 75 \Omega$			4.1	μs
t _f	Fall Time	All Devices	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V}, R_L = 100 \Omega$		2		μs
		CNY17XM/FXM	$I_F = 10 \text{mA}, V_{CC} = 5 \text{V}, R_L = 75 \Omega$			3.5	
SATURA	TED SWITCHING	TIMES		'			
t _{on}	Turn-on Time	CNY171M/F1M	$I_F = 20$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			5.5	μs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			8.0	
t _r	Rise Time	CNY171M/F1M	$I_F = 20$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			4.0	μs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω	V.		6.0	
t _d	Delay Time	CNY171M/F1M	$I_F = 20$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			5.5	μs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			8.0	
t _{off}	Turn-off Time	CNY171M/F1M	I _F = 20mA, V _{CE} = 0.4V			34	μs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	I _F = 10mA, V _{CE} = 0.4V			39	
t _f	Fall Time	CNY171M/F1M	$I_F = 20$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			20.0	μs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			24.0	
t _s	Storage Time	CNY171M/F1M	$I_F = 20$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			34.0	μs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω			39.0	

^{*}All typicals at T_A = 25°C

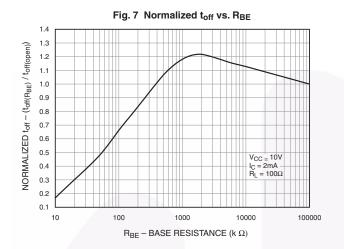
Notes:

- 1. Always design to the specified minimum/maximum electrical limits (where applicable).
- 2. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.
- 3. For test circuit setup and waveforms, refer to Figures 10 and 11.
- 4. For this test, Pins 1 and 2 are common, and Pins 4 are 5 are common.





Typical Performance Characteristics (Continued)



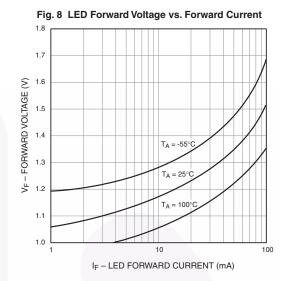
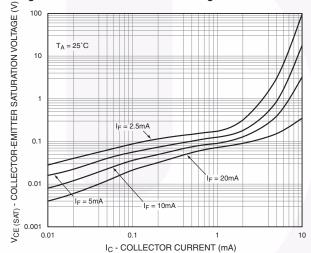


Fig. 9 Collector-Emitter Saturation Voltage vs Collector Current 10 0.1 = 20mA 0.01



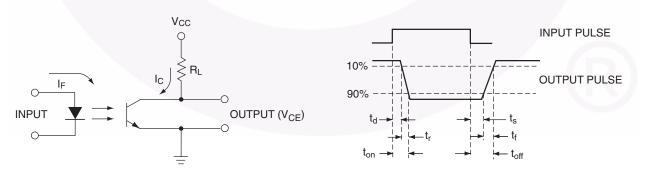
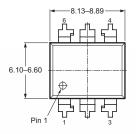


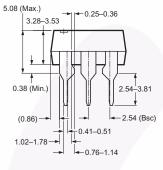
Figure 10. Switching Time Test Circuit

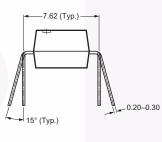
Figure 11. Switching Time Waveforms

Package Dimensions

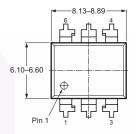
Through Hole

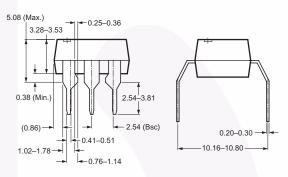




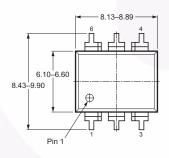


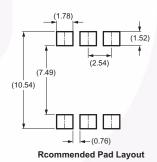
0.4" Lead Spacing

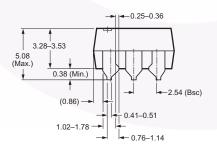


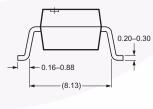


Surface Mount







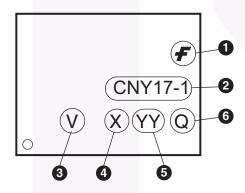


Note: All dimensions in mm.

Ordering Information

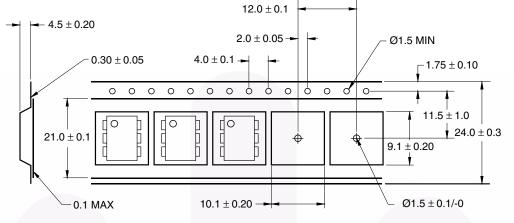
Option	Order Entry Identifier (Example)	Description
No option	CNY171M Standard Through Hole Device	
S	CNY171SM	Surface Mount Lead Bend
SR2	CNY171SR2M	Surface Mount; Tape and Reel
Т	CNY171TM	0.4" Lead Spacing
V	CNY171VM	IEC60747-5-2
TV	CNY171TVM	IEC60747-5-2, 0.4" Lead Spacing
SV	CNY171SVM	IEC60747-5-2, Surface Mount
SR2V CNY171SR2VM IEC60747-5-2, Surface Mount, Ta		

Marking Information



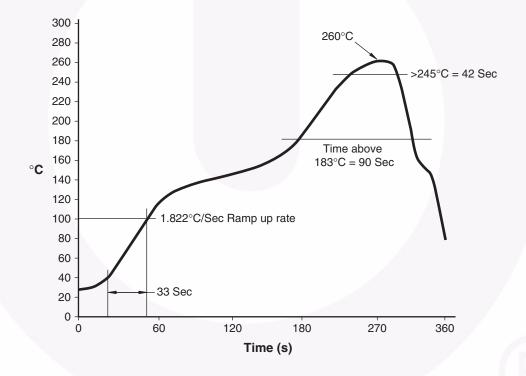
Definitions					
1	Fairchild logo				
2	Device number				
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)				
4	One digit year code, e.g., '7'				
5	Two digit work week ranging from '01' to '53'				
6	Assembly package code				

Carrier Tape Specification



User Direction of Feed ———

Reflow Profile







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Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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